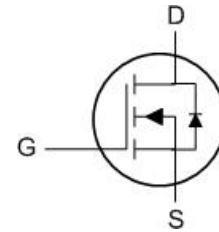




Features

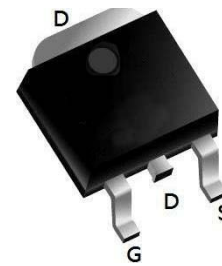
- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$



Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

TO252 Pin Configuration



Product Summary

BVDSS	R _{DS(ON)}	I _D
100V	61mΩ	15A

Absolute Maximum Ratings (T_C= 25°C unless otherwise specified):

Symbol	Parameter	Value	Units
V _{DSS}	Drain-to-Source Voltage	100	V
I _D	Continuous Drain Current	T _C = 25 °C	15
		T _C = 100 °C	10.7
I _{DM} ^{a1}	Pulsed Drain Current	80	A
E _{AS} ^{a2}	Single pulse avalanche energy	22	mJ
V _{GS}	Gate-to-Source Voltage	±20	V
P _D	Power Dissipation	46	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	150, -55 to 150	°C
T _L	Maximum Temperature for Soldering	260	°C

Thermal Characteristics:

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	2.7	°C/W



Electrical Characteristics (T_J= 25°C unless otherwise specified) :

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	--	--	V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 100V, V _{GS} = 0V	--	--	1	μA
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} = -20V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} = +20V	--	--	-100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.3	1.8	2.3	V
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =5A	--	61	75	mΩ
		V _{GS} =4.5V, I _D =4A	--	77	100	mΩ

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C _{iss}	Input Capacitance	V _{GS} =0V V _{DS} =50V f=1.0MHz	--	228	--	pF
C _{oss}	Output Capacitance		--	58	--	
C _{rss}	Reverse Transfer Capacitance		--	1.9	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D =10A, R _L =0.75Ω V _{DS} =50V V _{GS} = 10V R _G = 3Ω	--	8	--	ns
t _r	Rise Time		--	16	--	
t _{d(OFF)}	Turn-Off Delay Time		--	17	--	
t _f	Fall Time		--	14	--	
Q _g	Total Gate Charge	V _{GS} =10V	--	3.7	--	nC
Q _{gs}	Gate Source Charge	V _{DS} =50V	--	0.8	--	
Q _{gd}	Gate Drain Charge	I _D =10A	--	1	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I _S	Diode Forward Current	T _C =25 °C	--	--	15	A
V _{SD}	Diode Forward Voltage	I _S =0.5A, V _{GS} =0V	--	--	1.2	V
t _{rr}	Reverse Recovery time	I _S =10A, V _{DD} =50V di/dt=100A/μs	--	22	--	ns
Q _{rr}	Reverse Recovery Charge		--	18	--	nC

a¹: Repetitive rating; pulse width limited by maximum junction temperature

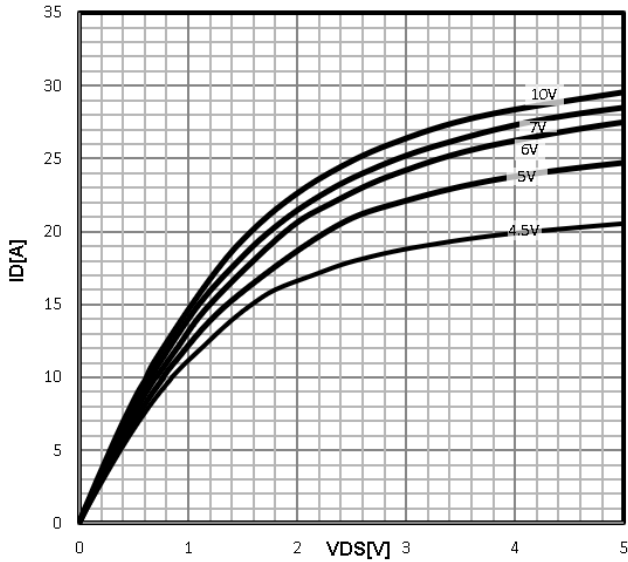
a²: L=5mH, R_g=25Ω, Starting T_J=25 °C



Characteristics Curve:

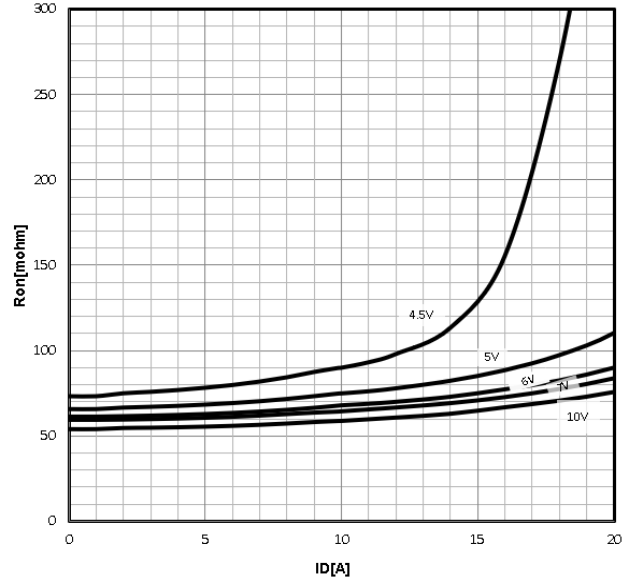
Typ. output characteristics

$$I_D = f(V_{DS})$$



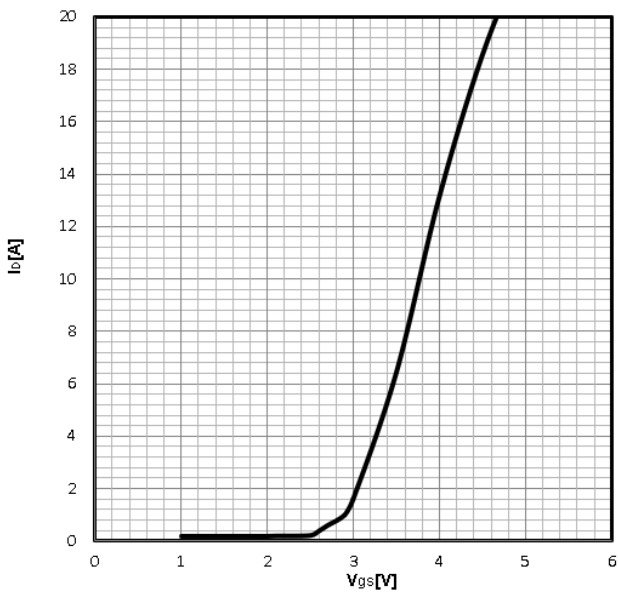
Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$



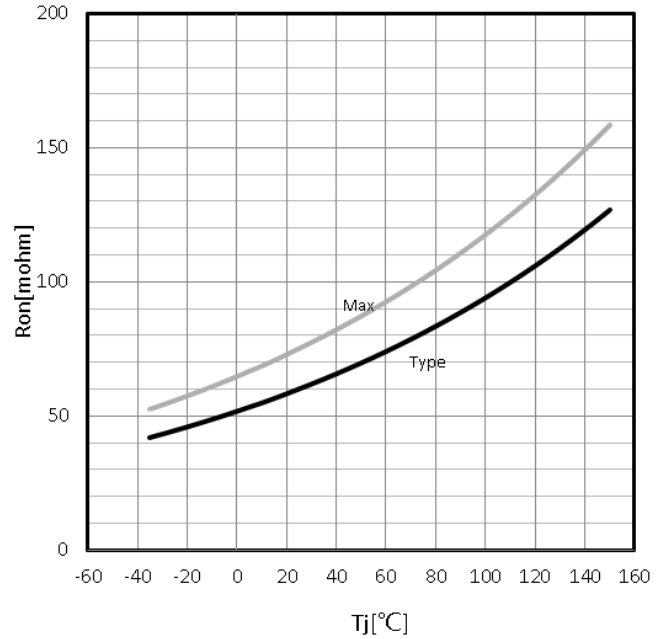
Typ. transfer characteristics

$$I_D = f(V_{GS})$$



Drain-source on-state resistance

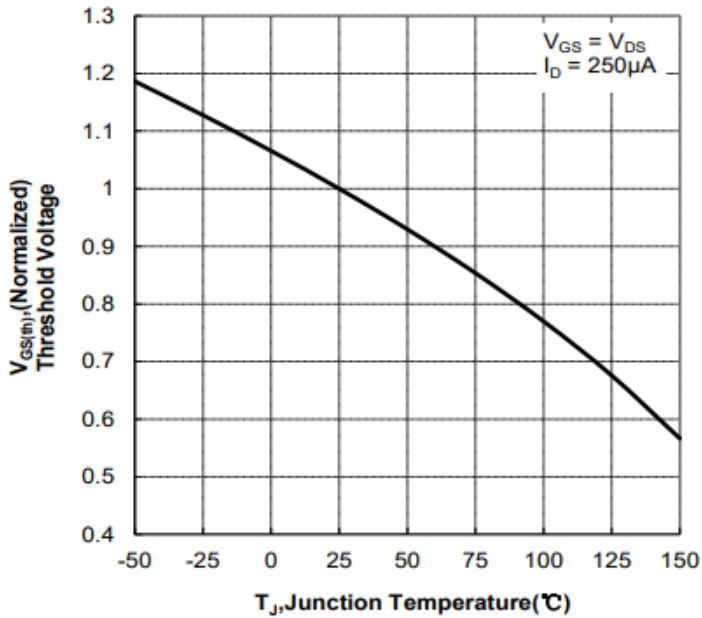
$$R_{DS(on)} = f(T_j); I_D = 5A; V_{GS} = 10V$$





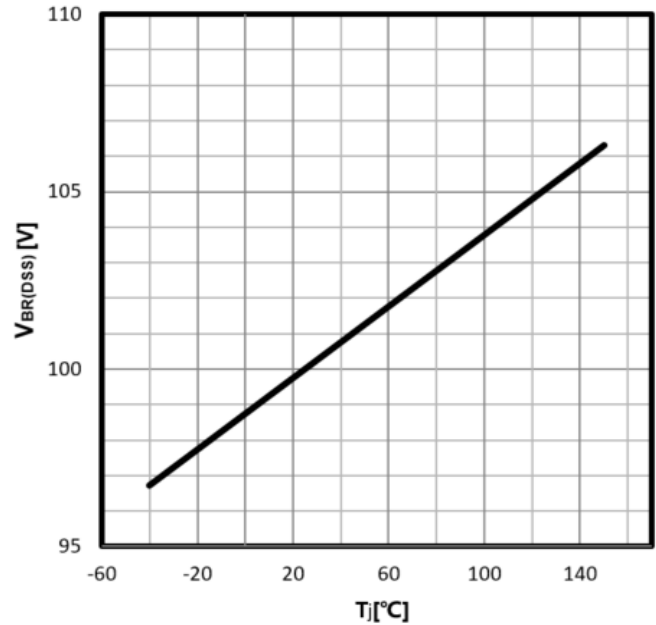
Gate Threshold Voltage

$$V_{TH} = f(T_j); I_D = 250\mu A$$



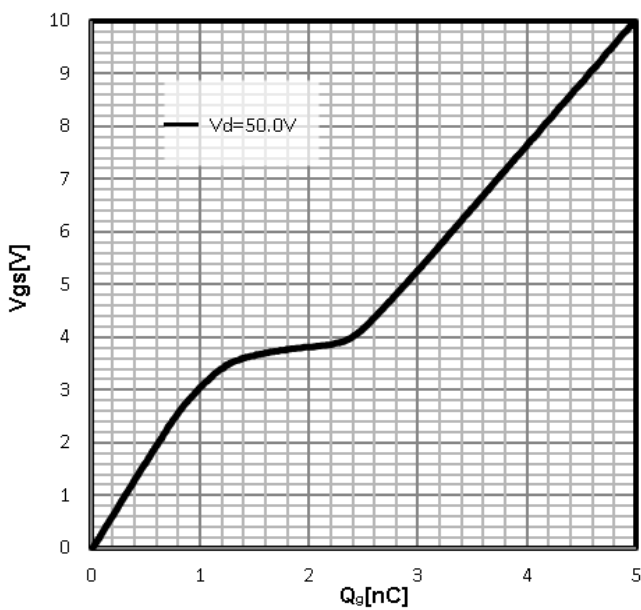
Drain-source breakdown voltage

$$V_{BR(DSS)} = f(T_j); I_D = 250\mu A$$



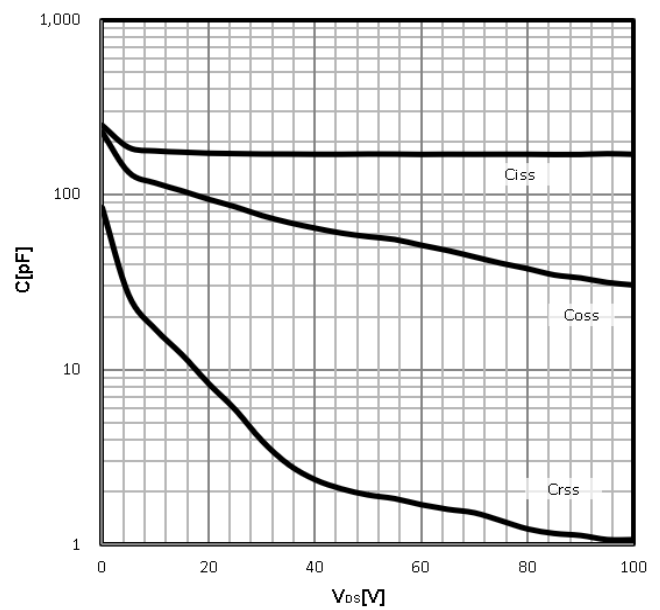
Typ. gate charge

$$V_{GS} = f(Q_g); I_D = 10A$$



Typ. capacitances

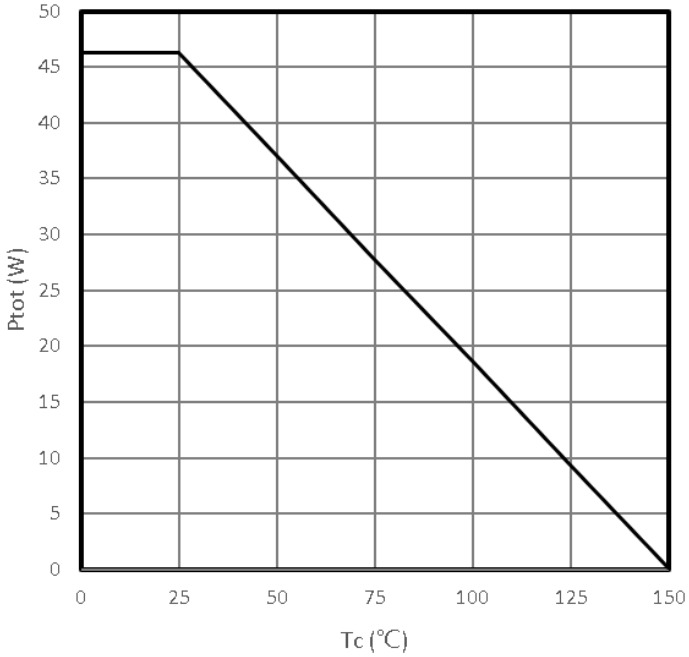
$$C = f(V_{DS}); V_{GS} = 0V; f = 1MHz$$





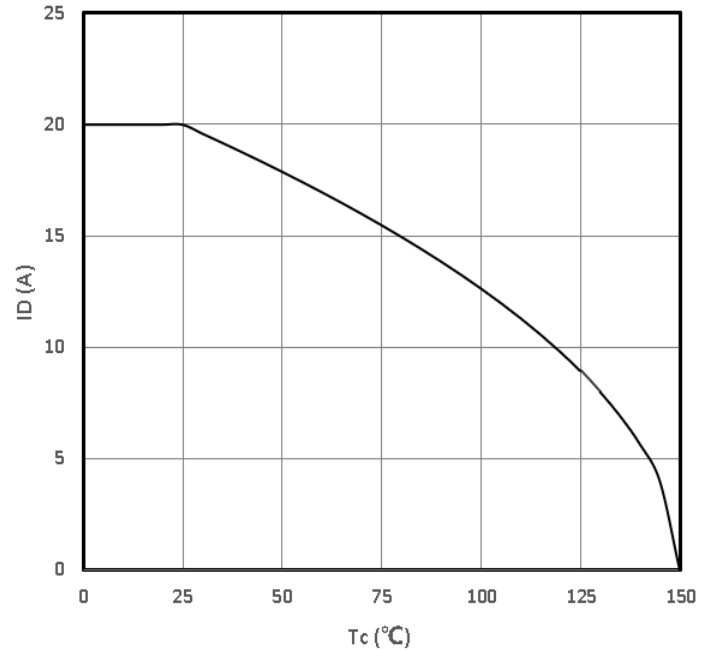
Power Dissipation

$P_{tot}=f(T_c)$



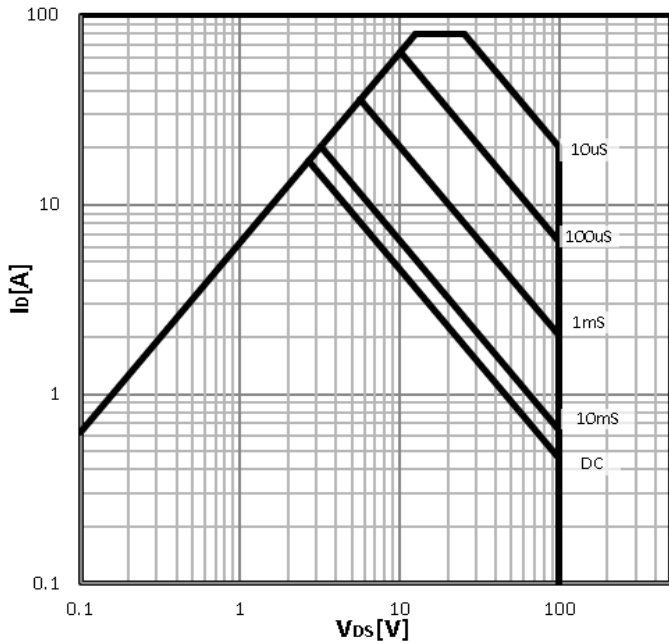
Maximum Drain Current

$I_D=f(T_c)$



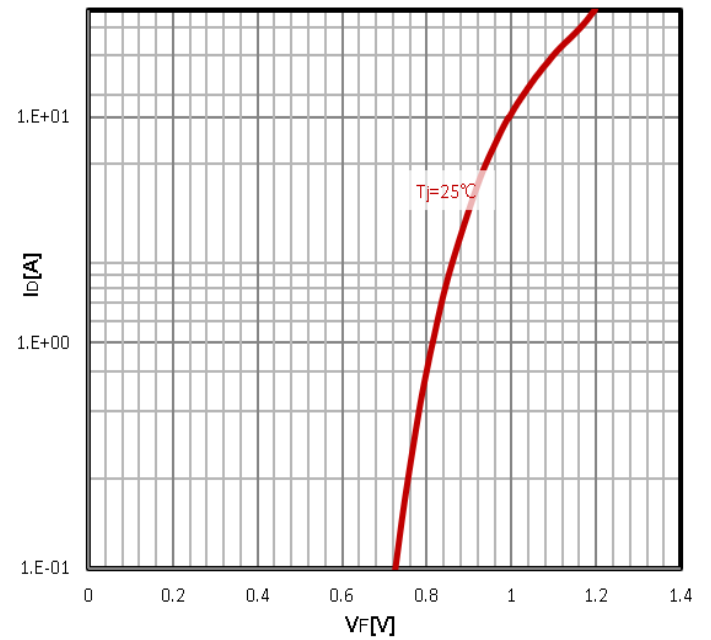
Safe operating area

$I_D=f(V_{DS})$



Body Diode Forward Voltage Variation

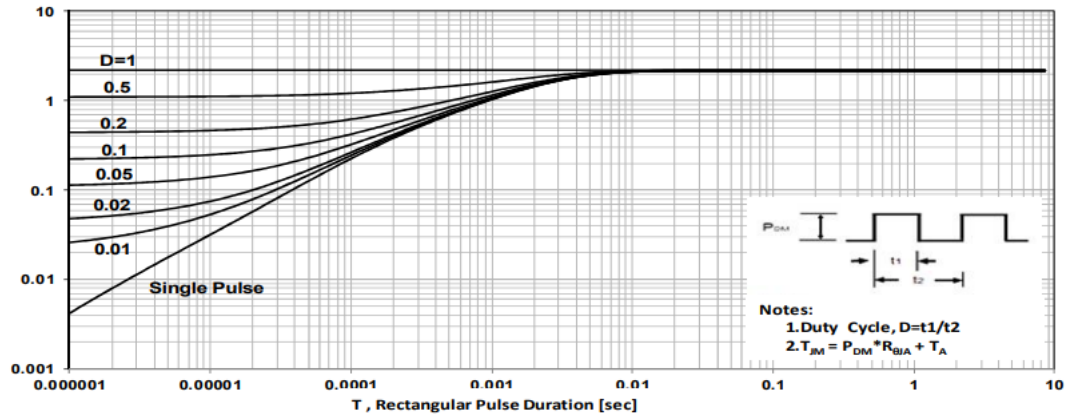
$I_F=f(V_{GS})$





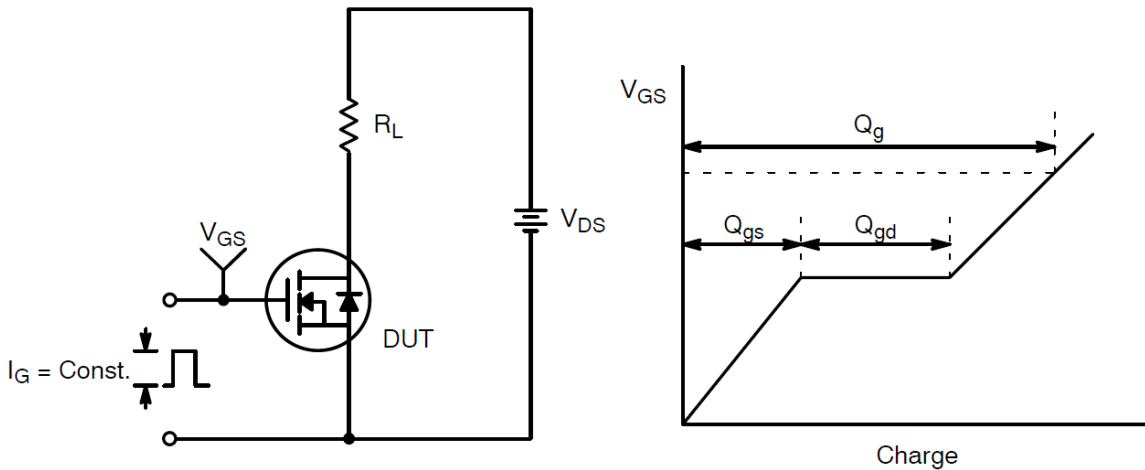
Max. transient thermal impedance

$$Z_{thJC}=f(t_p)$$

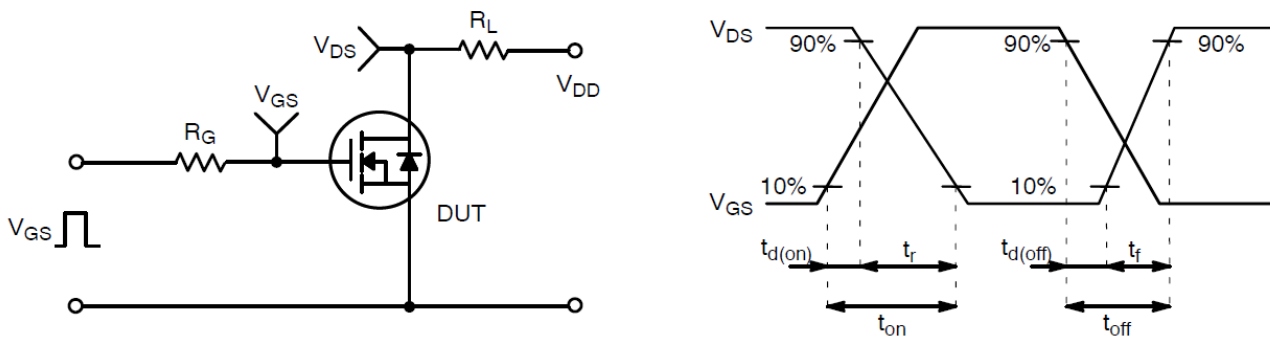




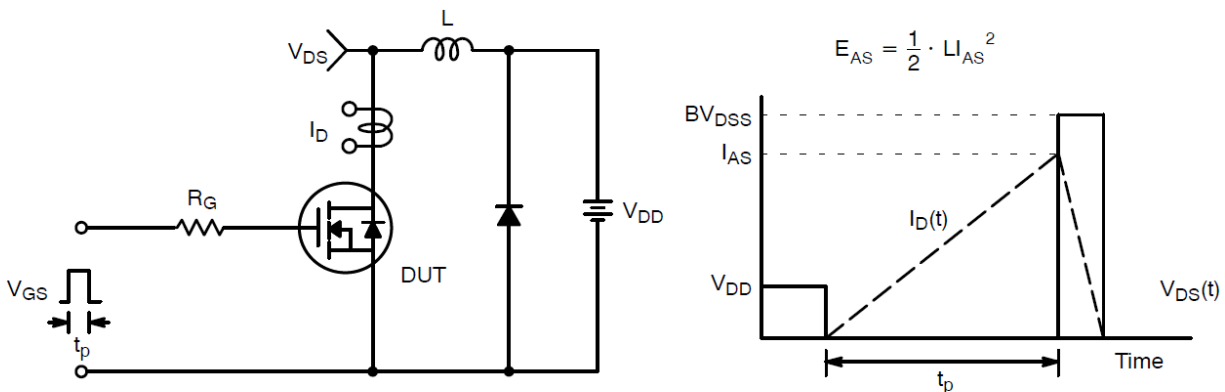
Test Circuit and Waveform:



Gate Charge Test Circuit & Waveform



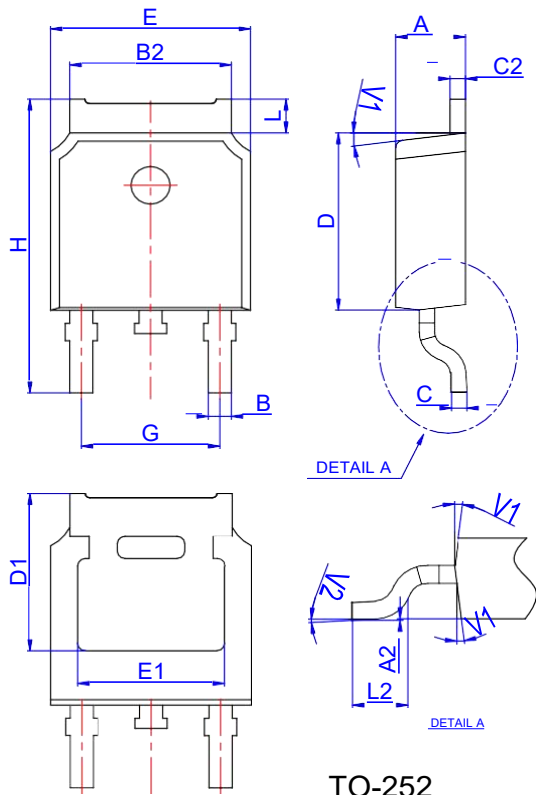
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



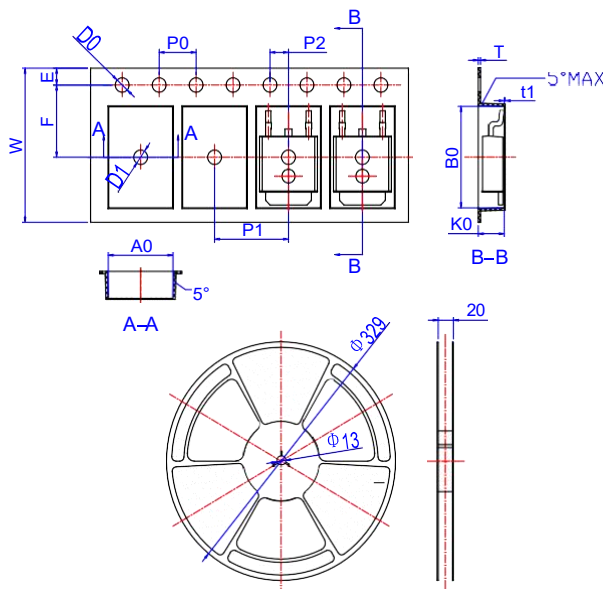
Package Mechanical Data TO 252



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°	0°		6°

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583



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